

# TRANSISTOR (PNP)

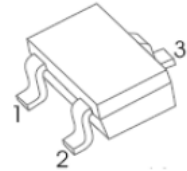
## BC856W/BC857W/BC858W

### FEATURES

- Ideally suited for automatic insertion
- For Switching and AF Amplifier Applications

### MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage		
	BC856W	-80	V
	BC857W	-50	
	BC858W	-30	
V <sub>CEO</sub>	Collector-Emitter Voltage		
	BC856W	-65	V
	BC857W	-45	
	BC858W	-30	
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current –Continuous	-0.1	A
P <sub>C*</sub>	Collector Power Dissipation	150	mW
R <sub>θJA</sub>	Thermal Resistance From Junction To Ambient	833	°C/W
T <sub>J</sub> , T <sub>stg</sub>	Operation Junction and Storage Temperature Range	-55~+150	°C



**SOT-323**

1. BASE
2. EMITTER
3. COLLECTOR

### DEVICE MARKING

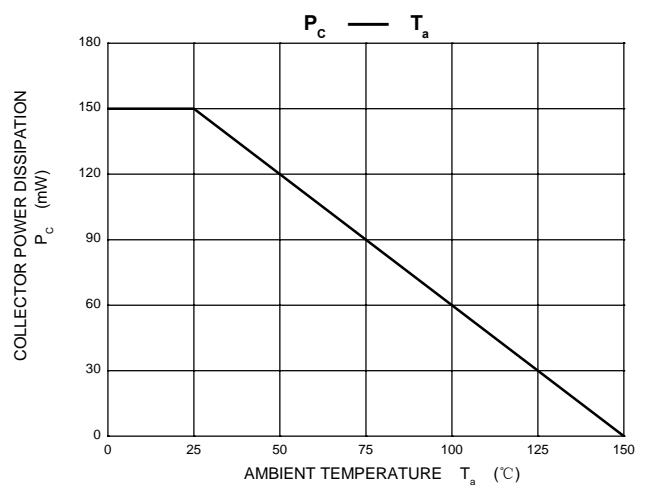
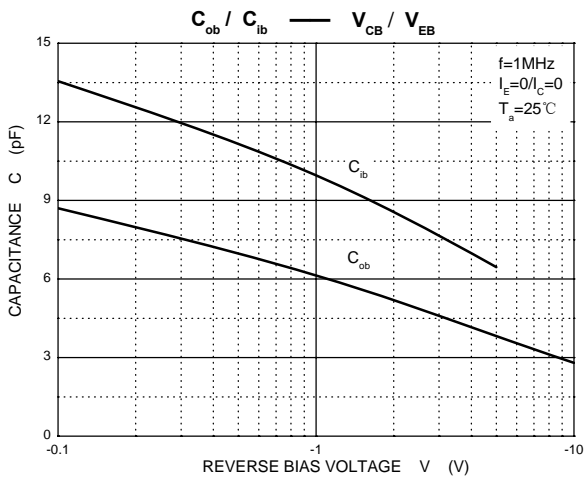
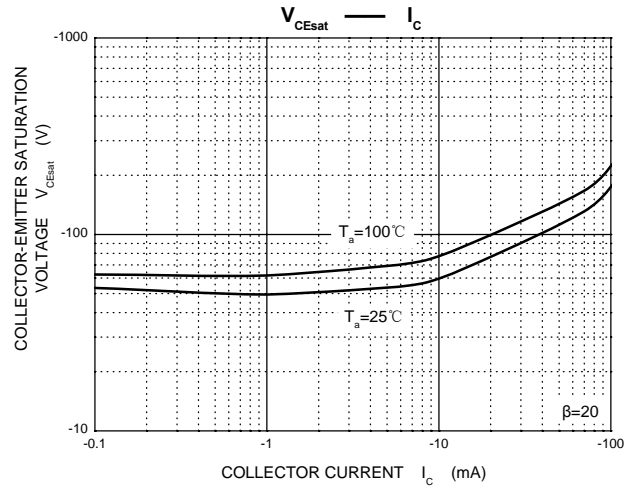
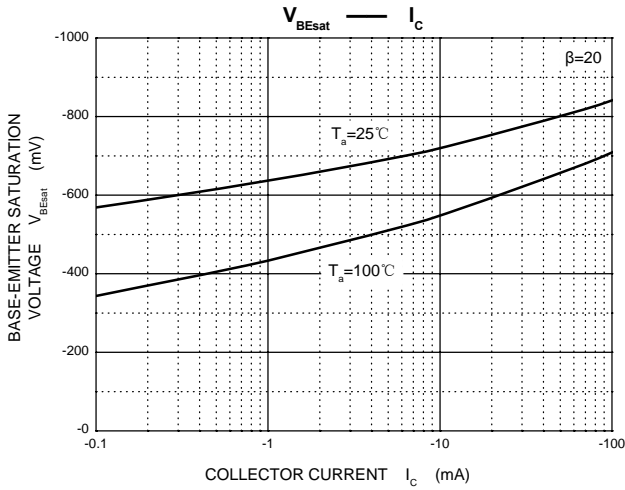
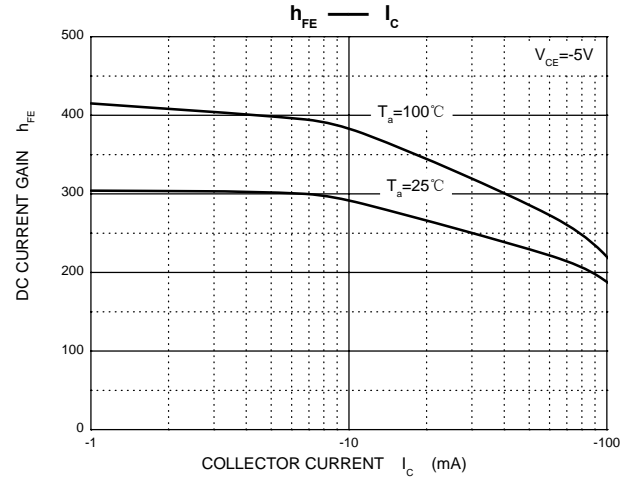
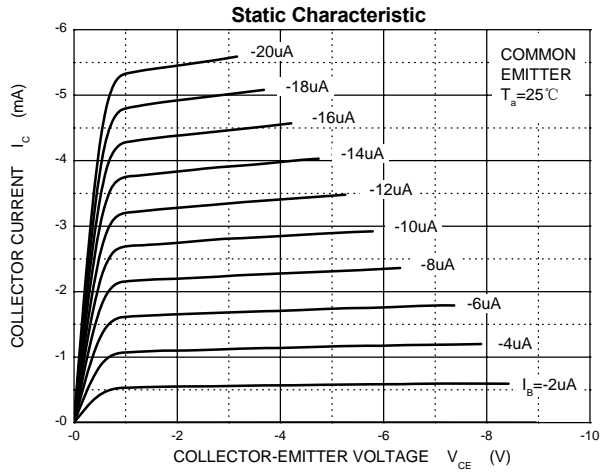
BC856AW=3A; BC856BW=3B;  
 BC857AW=3E; BC857BW=3F; BC857CW=3G;  
 BC858AW=3J; BC858BW=3K; BC858CW=3L

### ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	BC856W BC857W BC858W	V <sub>CB0</sub> I <sub>C</sub> = -10μA, I <sub>E</sub> =0	-80 -50 -30		V
Collector-emitter breakdown voltage	BC856W BC857W BC858W	V <sub>CEO</sub> I <sub>C</sub> = -10mA, I <sub>B</sub> =0	-65 -45 -30		V
Emitter-base breakdown voltage		V <sub>EBO</sub> I <sub>E</sub> = -1μA, I <sub>C</sub> =0	-5		V
Collector cut-off current		I <sub>CB0</sub> V <sub>CB</sub> = -30 V, I <sub>E</sub> =0		-15	nA
DC current gain	BC856AW, 857AW, 858AW BC856BW, 857BW, 858BW BC857CW, BC858CW	h <sub>FE</sub> V <sub>CE</sub> = -5V, I <sub>C</sub> = -2mA	125 220 420	250 475 800	
Collector-emitter saturation voltage		V <sub>CE(sat)</sub> I <sub>C</sub> =-100mA, I <sub>B</sub> = -5mA		-0.65	V
Base-emitter saturation voltage		V <sub>BE(sat)</sub> I <sub>C</sub> = -100mA, I <sub>B</sub> = -5mA		-1.1	V
Transition frequency		f <sub>T</sub> V <sub>CE</sub> = -5V, I <sub>C</sub> = -10mA f=100MHz	100		MHz
Collector capacitance		C <sub>ob</sub> V <sub>CB</sub> =-10V, f=1MHz		4.5	pF

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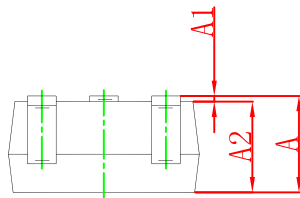
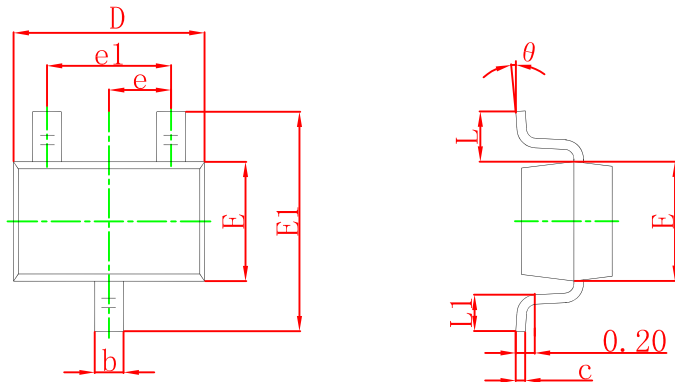
## Typical Characteristics



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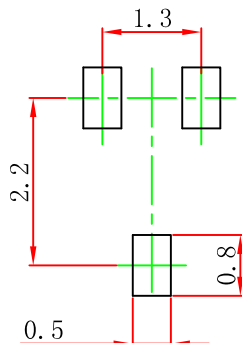
## BC856W/BC857W/BC858W

### SOT-323 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
theta	0°	8°	0°	8°

### SOT-323 Suggested Pad Layout



**Note:**

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.05$  mm.
3. The pad layout is for reference purposes only.